

# 2SC4543

Silicon NPN epitaxial planer type

For video amplifier

## Features

- High transition frequency  $f_T$ .
- Small collector output capacitance  $C_{ob}$ .
- Wide current range.

## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	110	V
Collector to emitter voltage	$V_{CER}^{*1}$	100	V
Collector to emitter voltage	$V_{CEO}$	50	V
Emitter to base voltage	$V_{EBO}$	3.5	V
Peak collector current	$I_{CP}$	300	mA
Collector current	$I_C$	150	mA
Collector power dissipation	$P_C^{*2}$	1.0	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C

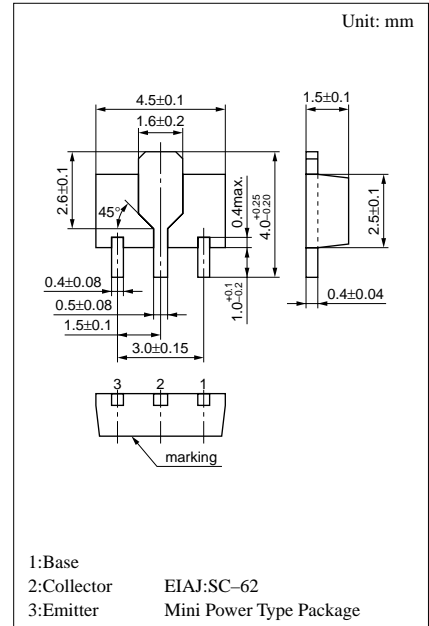
\*1  $R_{EB} = 1.2k\Omega$

\*2 Printed circuit board: Copper foil area of 1cm<sup>2</sup> or more, and the board thickness of 1.7mm for the collector portion

## Electrical Characteristics (Ta=25°C)

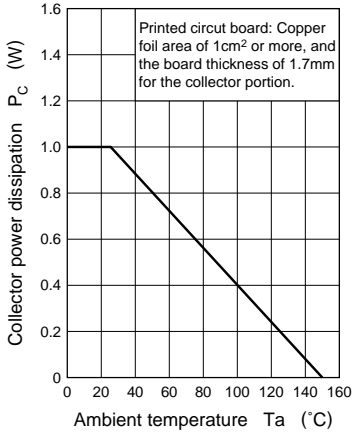
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CEO}$	$V_{CE} = 35V, I_B = 0$			10	$\mu A$
Collector to base voltage	$V_{CBO}$	$I_C = 100\mu A, I_E = 0$	110			V
Collector to emitter voltage	$V_{CER}$	$I_C = 500\mu A, R_{BE} = 470\Omega$	100			V
	$V_{CEO}$	$I_C = 1mA, I_B = 0$	50			V
Emitter to base voltage	$V_{EBO}$	$I_E = 100\mu A, I_C = 0$	3.5			V
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 5V, I_C = 100mA^*$	20			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 150mA, I_B = 15mA^*$			0.5	V
Transition frequency	$f_{T1}$	$V_{CB} = 10V, I_E = -10mA, f = 200MHz$		300		MHz
	$f_{T2}$	$V_{CB} = 10V, I_E = -110mA^*, f = 200MHz$		350		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 30V, I_E = 0, f = 1MHz$		3		pF

\* Pulse measurement

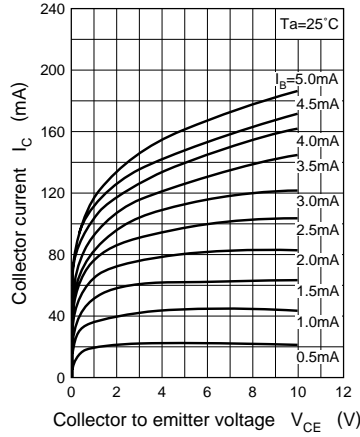


Marking symbol : 1F

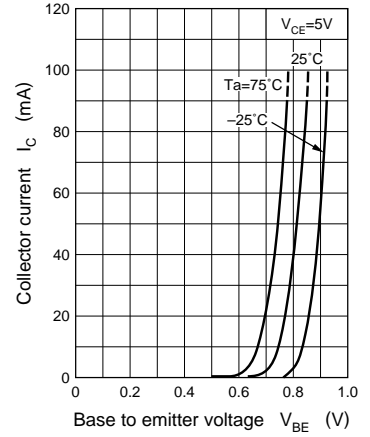
$P_C - T_a$



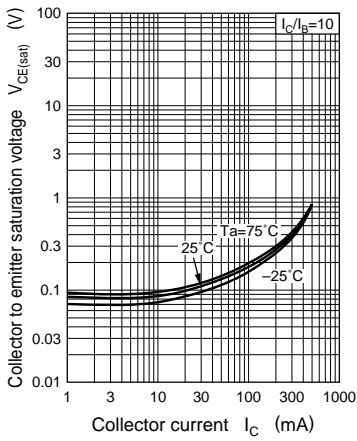
$I_C - V_{CE}$



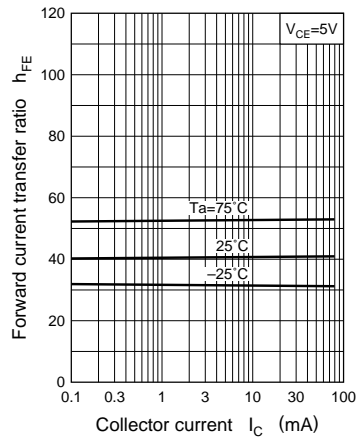
$I_C - V_{BE}$



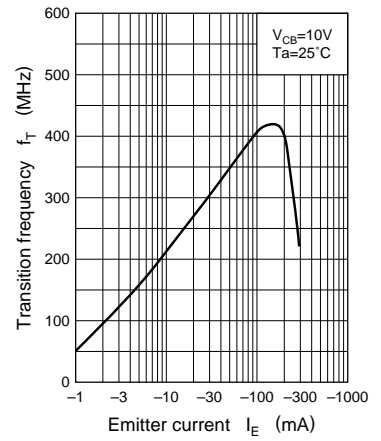
$V_{CE(sat)} - I_C$



$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$

